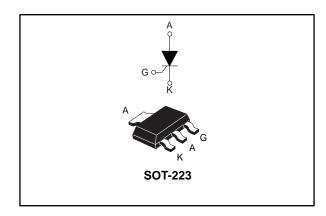
## **P0102MN**



## Sensitive 0.8 A SCR thyristor

Datasheet - production data



### **Features**

- I<sub>T(RMS)</sub> 0.8 A
- 125 °C max T<sub>i</sub>
- Low 0.2 mA gate current
- 600 V V<sub>DRM</sub>/V<sub>RRM</sub>
- ECOPACK®2 compliant component

### **Applications**

- Proximity sensors
- Gate driver for large thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Standby mode power supplies
- Residual current detector

## **Description**

Thanks to highly sensitive triggering levels, the 0.8 A P0102MN SCR thyristor is suitable for all applications where available gate current is limited. This device offers a high blocking voltage of 600 V, ideal for applications like interrupters circuits.

The surface mount SOT-223 package allows compact, SMD based designs for automated manufacturing.

**Table 1: Device summary** 

| Symbol                             | Value | Unit |  |
|------------------------------------|-------|------|--|
| I <sub>T(RMS)</sub>                | 0.8   | А    |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 600   | V    |  |
| lgт                                | 0.2   | mA   |  |
| T <sub>j</sub> max.                | 125   | °C   |  |

**Characteristics** P0102MN

#### **Characteristics** 1

Table 2: Absolute maximum ratings (limiting values),  $T_j$  = 25 °C unless otherwise specified

| Symbol                             | Parameter  | Value                 | Unit                     |                  |      |
|------------------------------------|--|-----------------------|--------------------------|------------------|------|
| I <sub>T(RMS)</sub>                | RMS on-state current (180 ° conduction   | T . 70 °C             | 0.8                      | Λ                |      |
| I <sub>T(AV)</sub>                 | Average on-state current (180 ° conduc   | tion angle)           | T <sub>amb</sub> = 70 °C | 0.5              | Α    |
| l                                  | (T : ::: L of oo)  |                       | $t_p = 8.3 \text{ ms}$   | 8                | Α    |
| I <sub>TSM</sub>                   |  |                       | $t_p = 10 \text{ ms}$    | 7                | A    |
| l <sup>2</sup> t                   | I <sup>2</sup> t value for fusing  | $t_p = 10 \text{ ms}$ | 0.24                     | A <sup>2</sup> s |      |
| dl/dt                              | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $I_T \le 100 \text{ ns}$ $f = 60 \text{ Hz}$ |                       | T <sub>j</sub> = 125 °C  | 50               | A/µs |
| V <sub>DRM</sub> /V <sub>RRM</sub> | Repetitive peak off-state voltage  |                       | T <sub>j</sub> = 125 °C  | 600              | V    |
| I <sub>GM</sub>                    | Peak gate current $t_p = 20 \mu s$   |                       | T <sub>j</sub> = 125 °C  | 1                | Α    |
| $P_{G(AV)}$                        | Average gate power dissipation $T_j = 125 \text{ °C}$  |                       |                          | 0.1              | W    |
| T <sub>stg</sub>                   | Storage junction temperature range   |                       |                          | -40 to +150      | °C   |
| T <sub>j</sub>                     | Operating junction temperature   | -40 to +125           | °C                       |                  |      |

Table 3: Electrical characteristics ( $T_j = 25$  °C unless otherwise specified)

| Symbol           | Test conditions  |               | Value | Unit |      |
|------------------|--|---------------|-------|------|------|
| lgт              | V <sub>D</sub> = 12 V. R <sub>L</sub> = 140 Ω                    | V 40V B 440 C |       | 200  | μΑ   |
| V <sub>G</sub> T | $VD = 12 \text{ V}, RL = 140 \Omega$                             |               | Max.  | 0.8  | V    |
| $V_{GD}$         | $V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, R_{GK} = 1000 \Omega$ | Min.          | 0.1   | V    |      |
| $V_{RG}$         | I <sub>RG</sub> = 10 μA  | Min.          | 8     | V    |      |
| lΗ               | $I_T = 50 \text{ mA}, R_{GK} = 1000 \Omega$                      | Max.          | 5     | mA   |      |
| IL               | $I_G$ = 1 mA, $R_{GK}$ = 1000 $\Omega$                           |               | Max.  | 6    | mA   |
| dV/dt            | $V_D = 67 \% V_{DRM}, R_{GK} = 1000 \Omega$ $T_j = 125 °C$       |               | Min.  | 75   | V/µs |

**Table 4: Static characteristics** 

| Symbol                             | Test condition   | Value                   | Unit |      |    |
|------------------------------------|--|-------------------------|------|------|----|
| V <sub>TM</sub>                    | $I_{TM} = 1.6 \text{ A}, t_p = 380 \ \mu \text{s}$                   | T <sub>j</sub> = 25 °C  | Max. | 1.95 | V  |
| Vто                                | Threshold voltage  | T <sub>j</sub> = 125 °C | Max. | 0.95 | V  |
| R <sub>D</sub>                     | Dynamic resistance   | T <sub>j</sub> = 125 °C | Max. | 600  | mΩ |
| 1 //                               | V V V D 4000 0   | T <sub>j</sub> = 25 °C  | Max  | 10   |    |
| I <sub>DRM</sub> /I <sub>RRM</sub> | IDRM/IRRM $V_D = V_{DRM}$ ; $V_R = V_{RRM}$ , $R_{GK} = 1000 \Omega$ |                         | Max. | 100  | μΑ |

**Table 5: Thermal parameters** 

| Symbol               | Parameter                | Value                      | Unit |      |
|----------------------|--------------------------|----------------------------|------|------|
| R <sub>th(j-t)</sub> | Junction to tab (DC)     |                            | 30   | 0044 |
| $R_{th(j-a)}$        | Junction to ambient (DC) | $S^{(1)} = 5 \text{ cm}^2$ | 60   | °C/W |

#### Notes:

Downloaded from Arrow.com.

 $^{(1)}S$  = copper surface under tab.

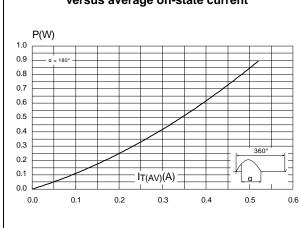
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P0102MN Characteristics

## 1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current



case temperature  $I_{T(AV)}(A)$ 1.1 D.C. (SOT-223) 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 T<sub>lead</sub> (°C) 0.0 0 25 50 100 125

Figure 2: Average and DC on-state current versus

Figure 3: Average and DC on-state current versus ambient temperature

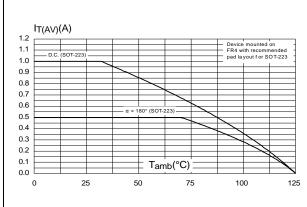


Figure 4: Relative variation of thermal impedance versus pulse duration

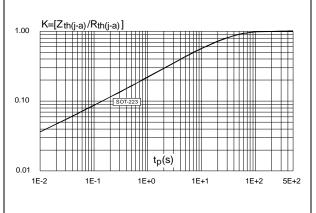


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

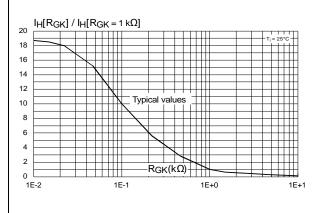
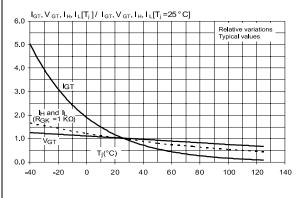


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)





Characteristics P0102MN

1.6 1.8 2.0

immunity versus gate-cathode resistance (typical values)  $dV/dt[R_{GK}] / dV/dt[R_{GK} = 1k\Omega]$ 10.0 Typical values1.0  $R_{GK}(k\Omega)$ 

0.2

0.4 0.6 0.8 1.0 1.2

Figure 7: Relative variation of static dV/dt

Figure 8: Relative variation of static dV/dt immunity versus junction temperature (typical values)

dV/dt[CGκ] / dV/dt[RGκ= 1kΩ, CGκ = 0 F]

v<sub>v=0.07 xV ores</sub>
RGκ= 1kΩ

Typical values

o 1 2 3 4 5 6 7

Figure 10: Non-repetitive surge peak on-state current for sinusoidal pulse (t<sub>p</sub> < 10 ms)

100.0

100.0

100.0

100.0

100.0

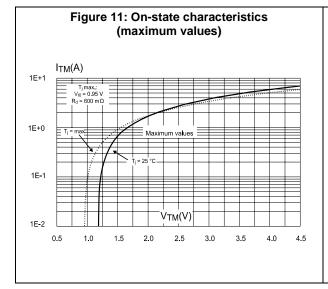
100.0

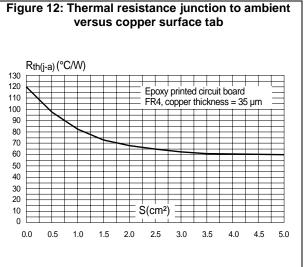
100.0

100.0

100.0

100.0





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P0102MN Package information

#### 2 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Lead-free package
- Halogen free molding resin
- Epoxy meets UL94, V0

#### **SOT-223 package information** 2.1

Figure 13: SOT-223 package outline

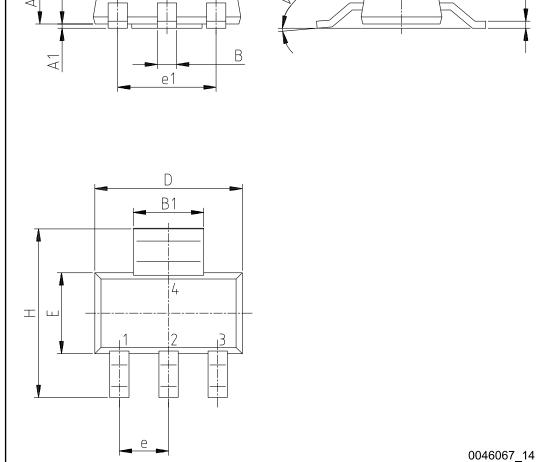




Table 6: SOT-223 package mechanical data

| Dim.             |      | Millimeters | -    |        | Inches <sup>(1)</sup> |        |
|------------------|------|-------------|------|--------|-----------------------|--------|
| Dilli.           | Min. | Тур.        | Max. | Min.   | Тур.                  | Max.   |
| А                |      |             | 1.8  |        |                       | 0.0709 |
| A1               | 0.02 |             | 0.1  | 0.0008 |                       | 0.0039 |
| В                | 0.6  | 0.7         | 0.85 | 0.0236 | 0.0276                | 0.0335 |
| B1               | 2.9  | 3           | 3.15 | 0.1142 | 0.1181                | 0.1240 |
| С                | 0.24 | 0.26        | 0.35 | 0.0094 | 0.0102                | 0.0138 |
| D <sup>(2)</sup> | 6.3  | 6.5         | 6.7  | 0.2480 | 0.2559                | 0.2638 |
| е                |      | 2.3         |      |        | 0.0906                |        |
| e1               |      | 4.6         |      |        | 0.1811                |        |
| E                | 3.3  | 3.5         | 3.7  | 0.1299 | 0.1378                | 0.1457 |
| Н                | 6.7  | 7.0         | 7.3  | 0.2638 | 0.2756                | 0.2874 |
| V                |      |             | 10°  |        |                       | 10°    |

### Notes:

3.3 6.4 1.5 4.6 0046067

Figure 14: SOT-223 recommended footprint (dimensions are in mm)

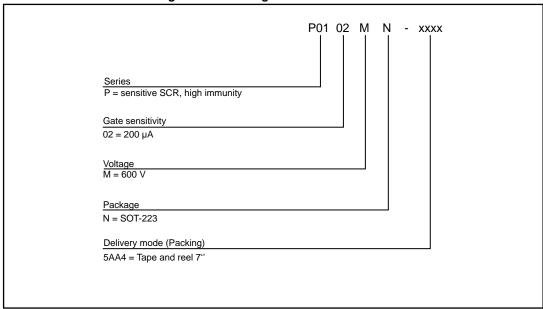
 $<sup>^{(1)}</sup>$ Inches dimensions given only for reference

 $<sup>^{(2)}</sup>$ Does not include mold flash or protusions. Mold flash or protusions must not exceed 0.15 mm (0.006 inches)

P0102MN Ordering information

# 3 Ordering information

Figure 15: Ordering information scheme



**Table 7: Ordering information** 

| Order code   | Marking | Package | Weight | Base qty. | Delivery mode    |
|--------------|---------|---------|--------|-----------|------------------|
| P0102MN 5AA4 | P2M     | SOT-223 | 0.12 g | 1000      | Tape and reel 7" |

# 4 Revision history

**Table 8: Document revision history** 

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 06-Oct-2017 | 1        | Initial release. |

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